

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



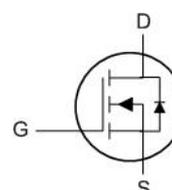
BVDSS	RDSON	ID
30V	3.5mΩ	100A

Description

The JH100N03F is the high cell density trenchd N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The JH100N03F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V_{DS}	Drain-Source Voltage	30		V
V_{GS}	Gate-Source Voltage	±20		V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	100		A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50		A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	30	19	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	25	16	A
I_{DM}	Pulsed Drain Current ²	162		A
EAS	Single Pulse Avalanche Energy ³	144.7		mJ
I_{AS}	Avalanche Current	53.8		A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	62.5		W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	6	2.42	W
T_{STG}	Storage Temperature Range	-55 to 175		°C
T_J	Operating Junction Temperature Range	-55 to 175		°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	---	25	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.4	°C/W

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} = 0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =10V, I _D =30A	-	3.5	4.7	mΩ
		V _{GS} =4.5V, I _D =20A	-	7.0	10	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f = 1.0MHz	-	2100	-	pF
C _{oss}	Output Capacitance		-	326	-	pF
C _{rss}	Reverse Transfer Capacitance		-	282	-	pF
Q _g	Total Gate Charge	V _{DS} =15V, I _D =30A, V _{GS} =10V	-	45	-	nC
Q _{gs}	Gate-Source Charge		-	3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	15	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =15V, I _D =30A, R _{GEN} =3Ω, V _{GS} =10V	-	21	-	ns
t _r	Turn-on Rise Time		-	32	-	ns
t _{d(off)}	Turn-off Delay Time		-	59	-	ns
t _f	Turn-off Fall Time		-	34	-	ns
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	50	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	200	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =30A	-	-	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=100A/μs	-	15	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	4	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_G=10V, R_G=25 Ω, L=0.5mH, I_{AS}=18.4A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

Figure 1: Output Characteristics

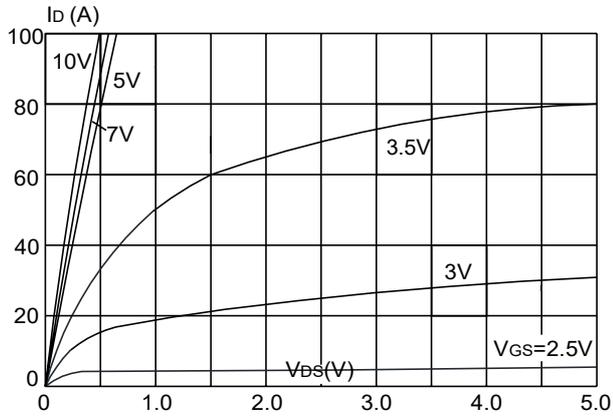


Figure 2: Typical Transfer Characteristics

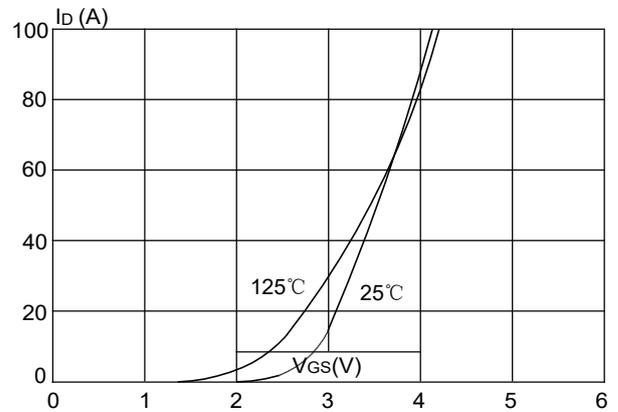


Figure 3: On-resistance vs. Drain Current

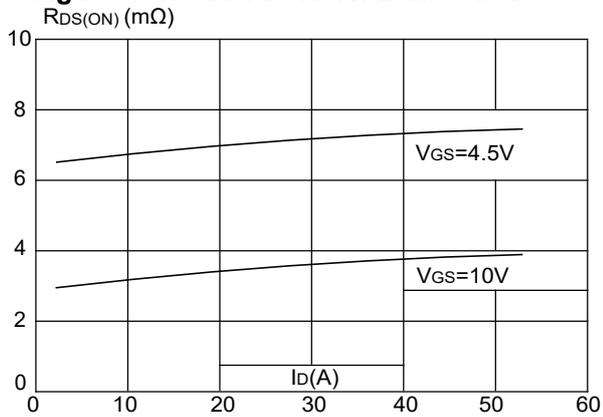


Figure 4: Body Diode Characteristics

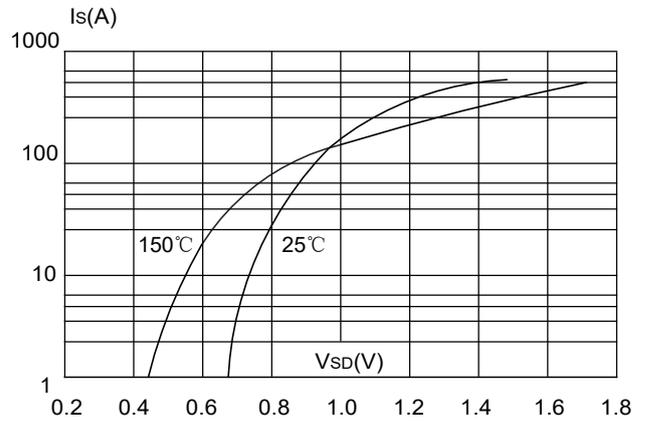


Figure 5: Gate Charge Characteristics

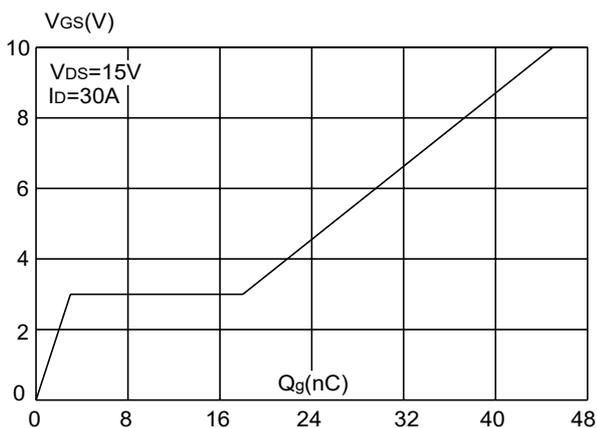


Figure 6: Capacitance Characteristics

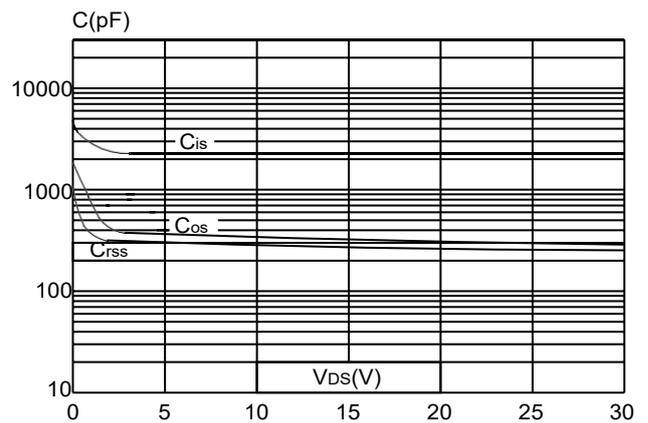


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

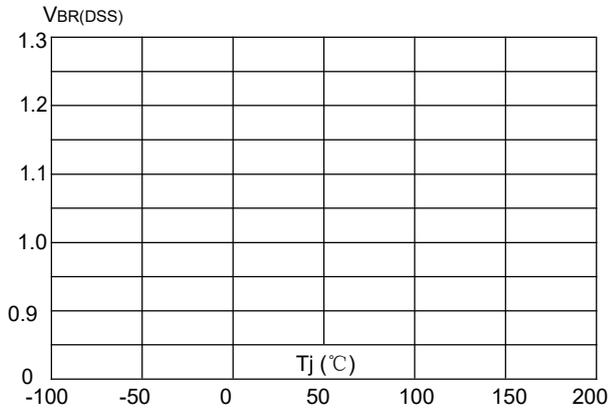


Figure 8: Normalized on Resistance vs. Junction Temperature

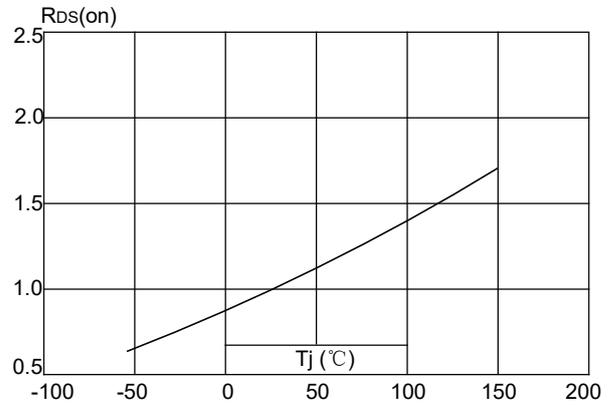


Figure 9: Maximum Safe Operating Area

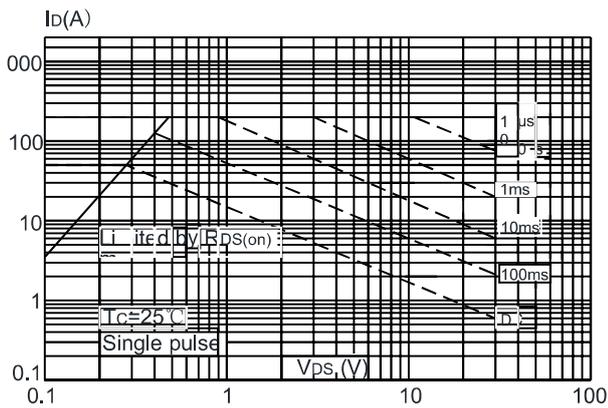


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

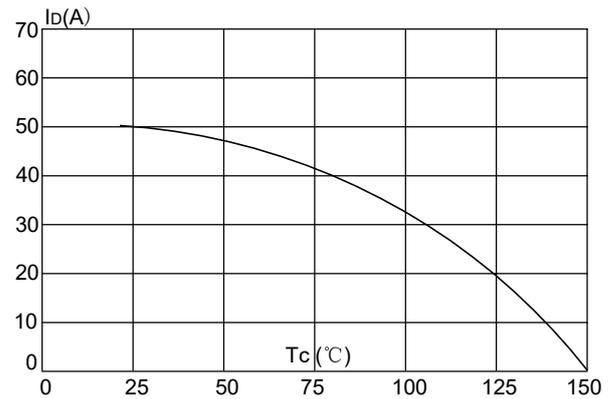
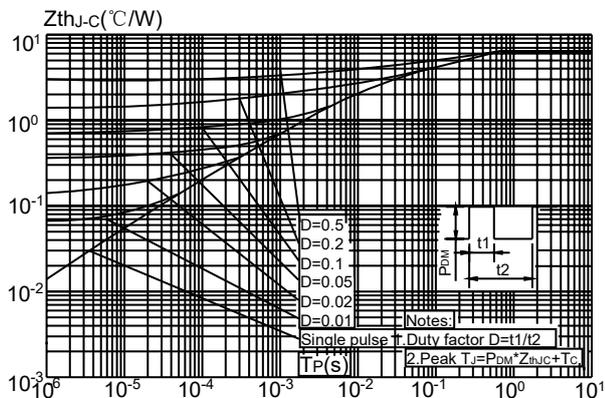


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (PDFN3.3*3.3-8L)



Test Circuit

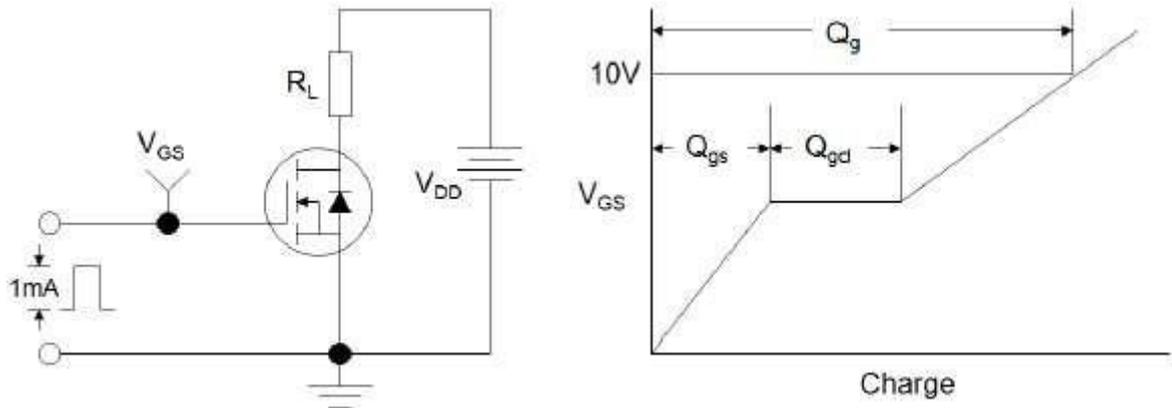


Figure1:Gate Charge Test Circuit & Waveform

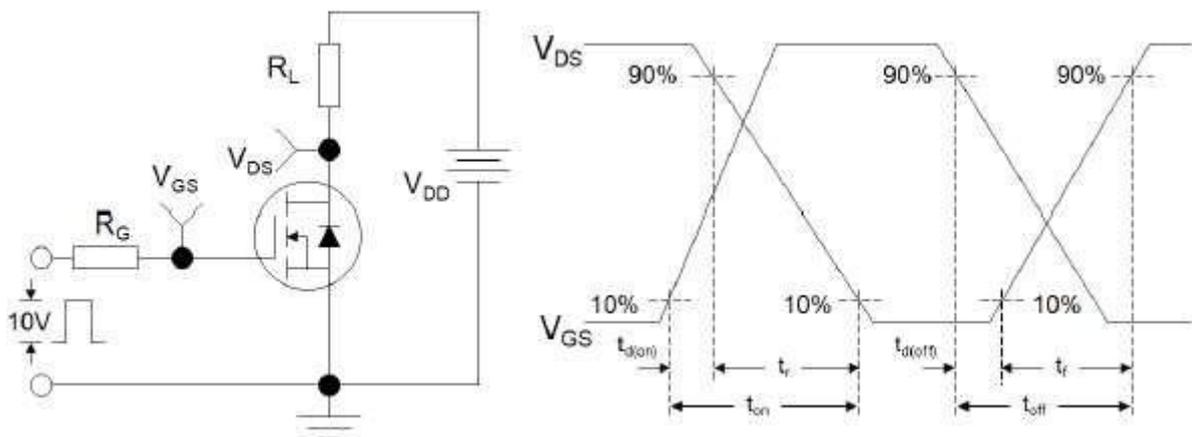


Figure 2: Resistive Switching Test Circuit & Waveforms

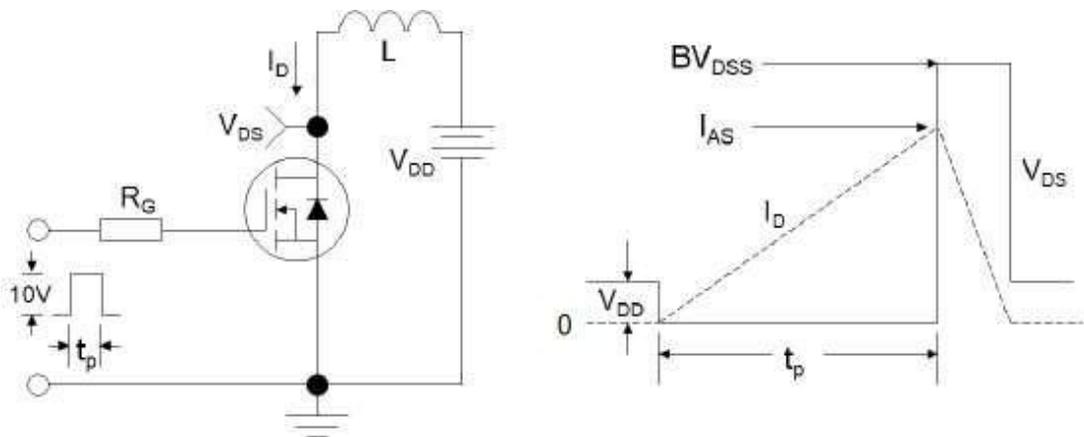
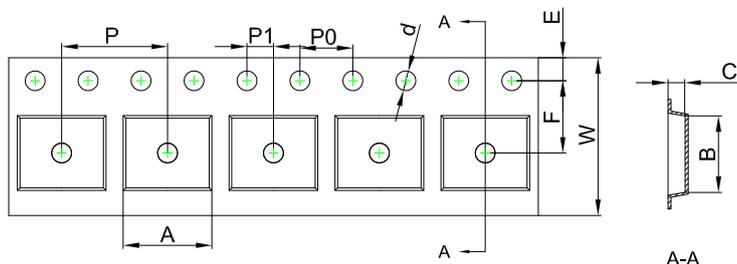


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

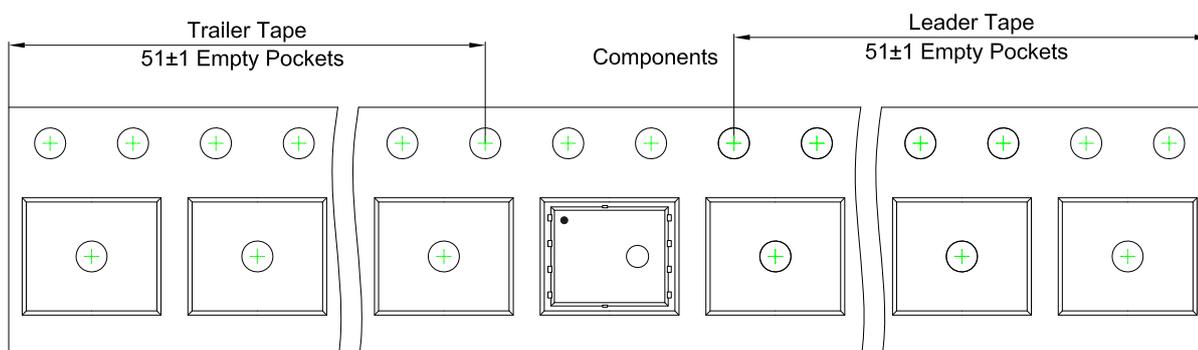
PDFN5×6 Tape and Reel

PDFN5×6 Embossed Carrier Tape

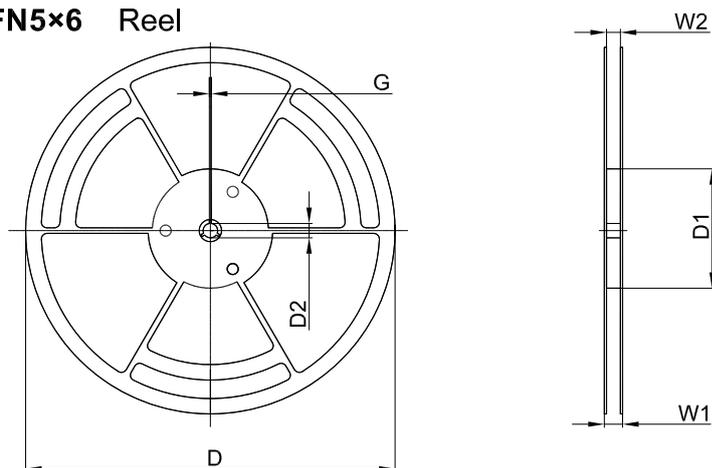


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFN5×6	6.30	5.30	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5×6 Tape Leader and Trailer

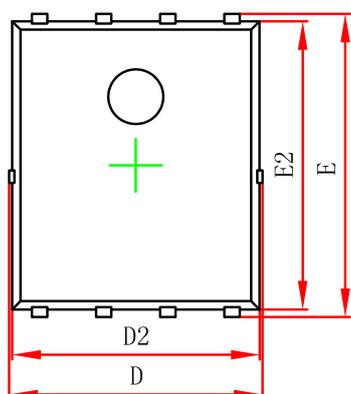


PDFN5×6 Reel

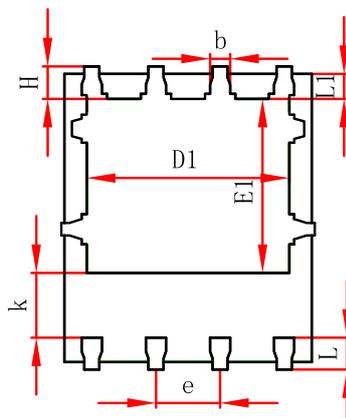


Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13" Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

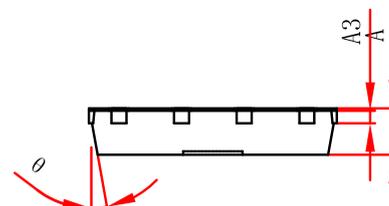
REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

DISCLAIMER

JHG PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with JHG products. You are solely responsible for

- (1) selecting the appropriate JHG products for your application;
- (2) designing, validating and testing your application;
- (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements.

These resources are subject to change without notice. JHG grants you permission to use these resources only for development of an application that uses the JHG products described in the resource. Other reproduction and display of these resources are prohibited. No license is granted to any other JHG intellectual property right or to any third party intellectual property right. JHG disclaims responsibility for, and you will fully indemnify JHG and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.